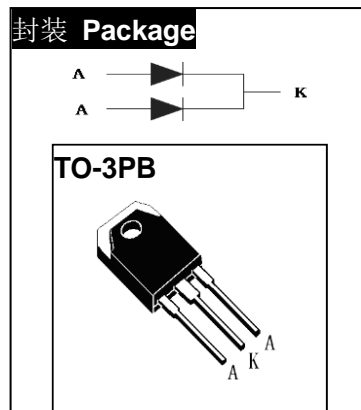




30F60AB3

主要参数 MAIN CHARACTERISTICS

IF(AV)	15×2 A
VRRM	600 V
Tj(max)	150°C
VF(typ)	1.4V
trr (typ)	29ns



用途

- 吸收回路
- 开关电源
- UPS
- 高频开关器件并联二极管

APPLICATIONS

- Snubber diode
- Switch power supply
- UPS
- Antiparalle Diode for high frequency switching devices

产品特性

- 低功耗，高效率
- 高可靠性
- 环保（RoHS）产品

FEATURES

- Low power loss, high efficiency
- High reliability
- RoHS product

订货信息 ORDER MESSAGE

订货型号 Order codes		印记 Marking	封装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen Free-Tube		
30F60AB3-GD-B	30F60AB3-GD-BR	30F60AB3	TO-3PB

绝对最大额定值 ABSOLUTE RATINGS ($T_c=25^\circ\text{C}$)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
最大反向重复峰值电压 Repetitive peak reverse voltage	V_{RRM}	600	V
最大反向工作峰值电压 Working Peak Reverse Voltage	V_{RWM}	600	V
平均正向整流电流 $T_c=100^\circ\text{C}$ Average Forward Rectified Current	Per Package $I_{F(AV)}$	30	A
	Per Diode	15	A
非重复浪涌正向电流 Non-Repetitive Surge Forward Current $t=10\text{ms}$	I_{FSM}	180	A
雪崩能量 Avalanche Energy(per diode) $L=40\text{mH}$	E_{AVL}	20	mJ
结温 Junction Temperature	T_j	-50~+150	$^\circ\text{C}$
储存温度 Storage temperature range	T_{STG}	-50~+150	$^\circ\text{C}$

电特性 ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise specified) per diode

项 目 Parameter	测试条件 Tests conditions	最小值 Value(min)	典型值 Value(typ)	最大值 Value(max)	单 位 Unit
V_R	$I_R=50\mu\text{A}$	600	680		V
I_R	$T_j=25^\circ\text{C}$			10	μA
	$T_j=125^\circ\text{C}$			250	μA
V_F	$T_j=25^\circ\text{C}$		1.4	1.8	V
	$T_j=125^\circ\text{C}$		1.2	1.6	V
C_j	$V_R=4.0\text{V}$, $f=1.0\text{MHz}$		100		pF
T_{rr}	$I_F=1\text{A}$, $V_R=30\text{V}$, $di_F/dt=-200\text{A}/\mu\text{s}$		29	45	ns
T_{rr}	$I_F=0.5\text{A}$, $I_R=1.0\text{A}$, $I_{RR}=0.25\text{A}$		27	40	ns
T_{rr}	$I_F=15\text{A}$, $V_R=400\text{V}$, $di_F/dt=200\text{A}/\mu\text{s}$		165		ns
I_{RM}	$T_j=125^\circ\text{C}$		6.2		A

热特性 THERMAL CHARACTERISTICS

项 目 Parameter	符 号 Symbol	最大值 Value(max)	单 位 Unit
结到管壳的热阻 Thermal Resistance Junction to Case	$R_{th(j-c)}$	0.8	$^\circ\text{C}/\text{W}$





特征曲线 ELECTRICAL CHARACTERISTICS (curves)

Fig.1 TYPICAL FORWARD CHARACTERISTICS

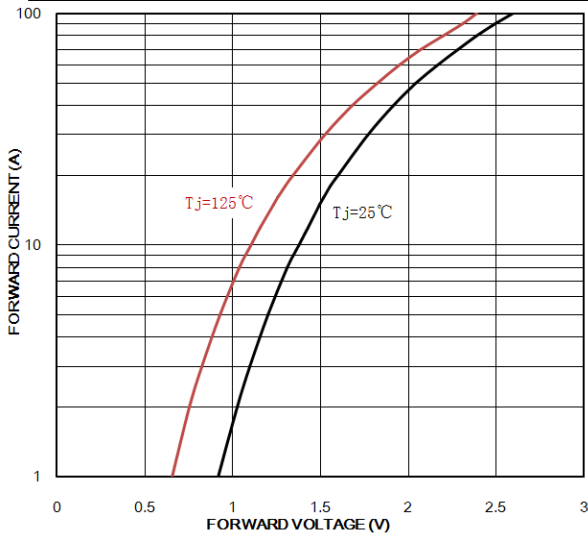


Fig.2 TYPICAL REVERSE CHARACTERISTICS

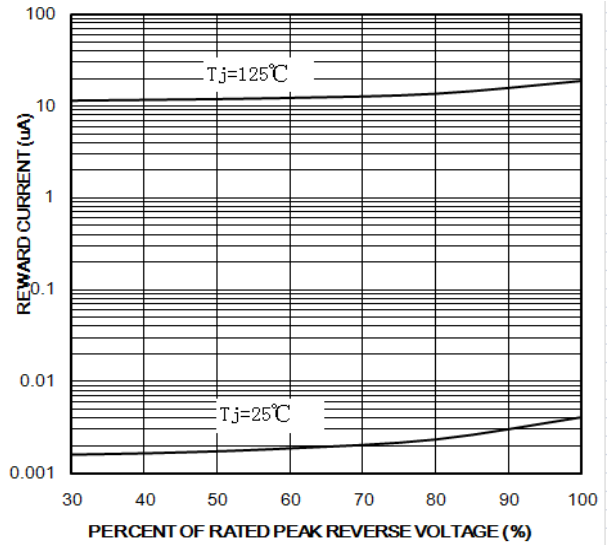


Fig.3 FORWARD CURRENT DERATING CURVE

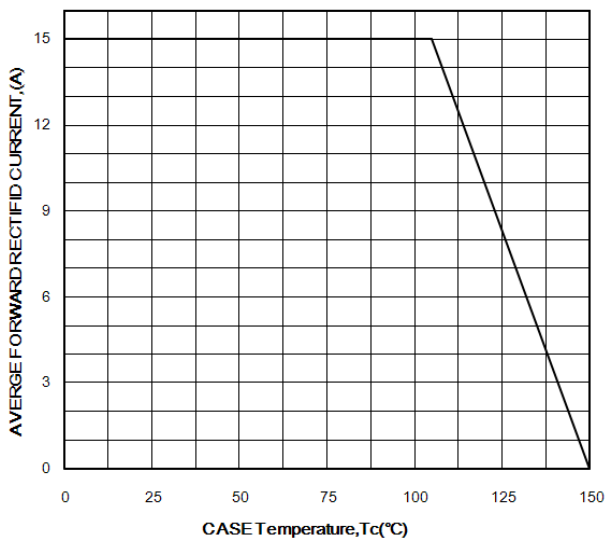


Fig.4 TYPICAL JUNCTION CAPACITANCE

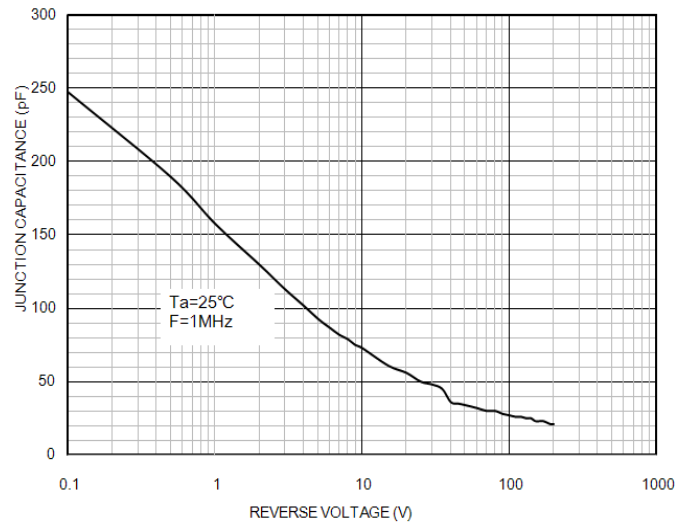


Fig.5 Reverse recovery time versus diF/dt

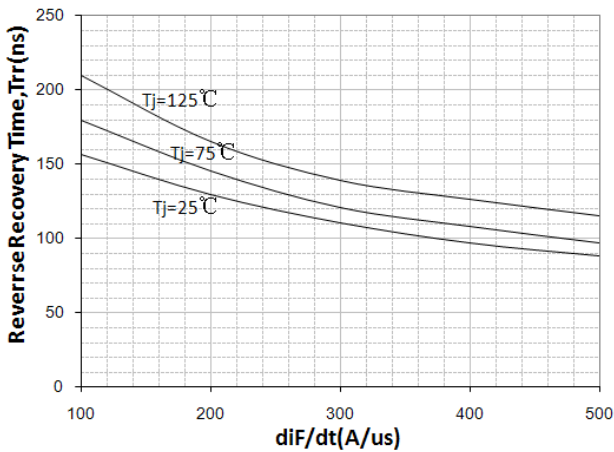
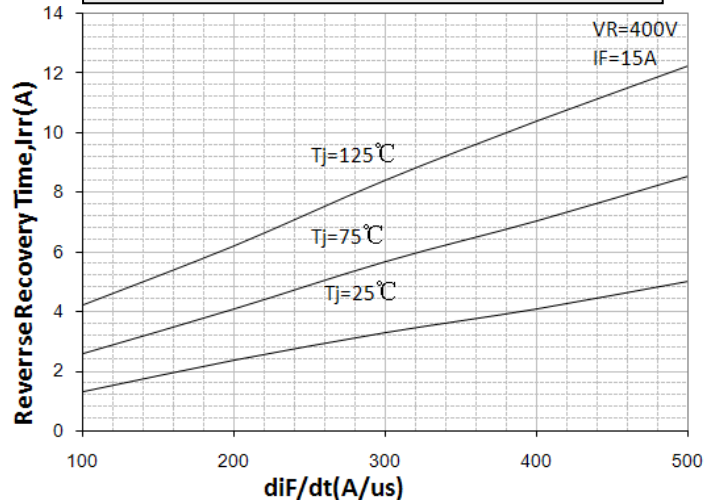


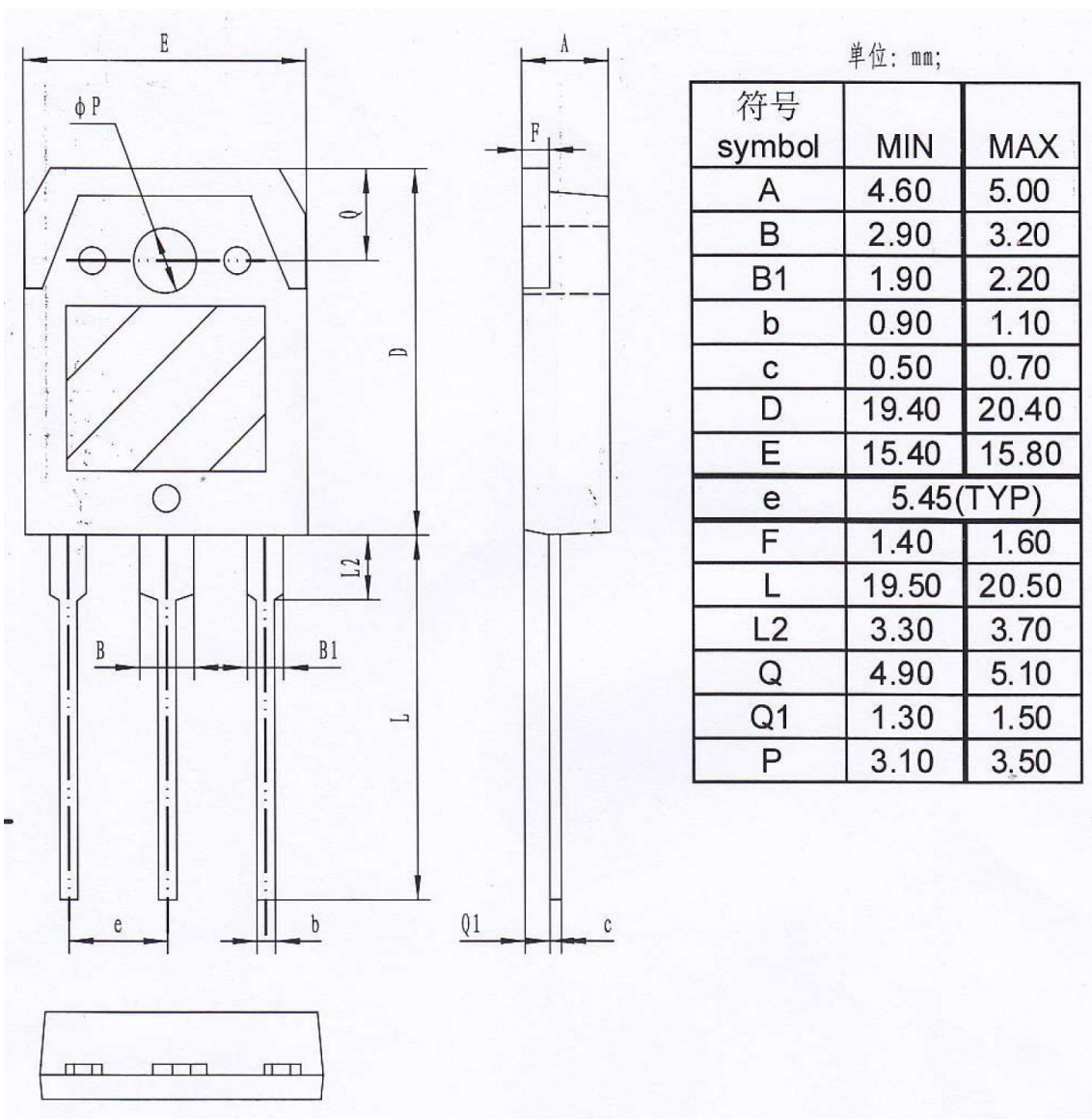
Fig.6 Peak reverse recovery current versus diF/dt





TO-3PB

单位 Unit : mm





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2. 购买时请认清公司商标，如有疑问请与公司本部联系。
3. 在电路设计时请不要超过器件的绝对最大额定值，否则会影响整机的可靠性。
4. 本说明书如有版本变更不另外告知。

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2. We strongly recommend customers check carefully on the trademark when buying our product, if there is any question, please don't be hesitate to contact us.
3. Please do not exceed the absolute maximum ratings of the device when circuit designing.
4. Jilin Sino-microelectronics co., Ltd reserves the right to make changes in this. specification sheet and is subject to change without prior notice.

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